SGS-THOMSON MICROELECTRONICS

BUF410A

HIGH VOLTAGE FAST-SWITCHING NPN POWER TRANSISTOR

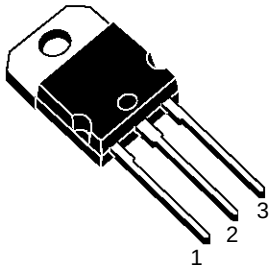
- SGS-THOMSON PREFERRED SALESTYPE
- HIGH VOLTAGE CAPABILITY
- VERY HIGH SWITCHING SPEED
- MINIMUM LOT-TO-LOT SPREAD FOR RELIABLE OPERATION
- LOW BASE-DRIVE REQUIREMENTS

APPLICATIONS:
- SWITCH MODE POWER SUPPLIES
- MOTOR CONTROL

DESCRIPTION

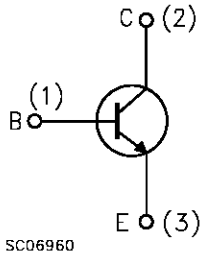
The BUF410A is manufactured using High Voltage Multi Epitaxial Planar technology for high switching speeds and high voltage capacity. They use a Cellular Emitter structure with planar edge termination to enhance switching speeds while maintaining a wide RBSOA.

The BUF series is designed for use in high-frequency power supplies and motor control applications.



TO-218

INTERNAL SCHEMATIC DIAGRAM



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V_{CEV}	Collector-Emitter Voltage (V_{BE} = -1.5 V)	1000	V
V_{CEO}	Collector-Emitter Voltage (I_B = 0)	450	V
V_{EBO}	Emitter-Base Voltage (I_C = 0)	7	V
I_C	Collector Current	15	A
I_{CM}	Collector Peak Current (t_p < 5 ms)	30	A
I_B	Base Current	3	A
I_{BM}	Base Peak Current (t_p < 5 ms)	4.5	A
P_{tot}	Total Dissipation at T_c = 25 °C	125	W
T_{stg}	Storage Temperature	-65 to 150	°C
T_j	Max Operation Junction Temperature	150	°C

THERMAL DATA

$R_{thj\text{-}case}$	Thermal Resistance Junction-Case	Max	1	°C/W

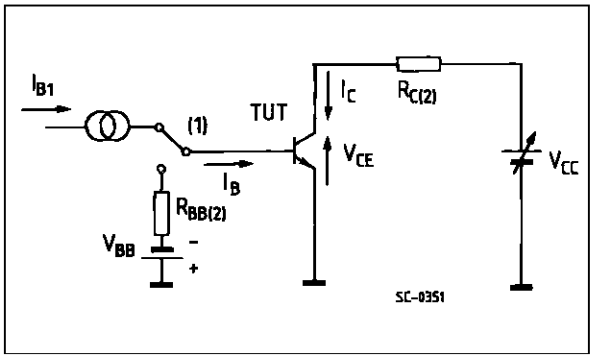
ELECTRICAL CHARACTERISTICS (T_{case} = 25 °C unless otherwise specified)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
I_{CER}	Collector Cut-off Current (R_{BE} = 100 Ω)	$V_{CE} = V_{CEV}$ $V_{CE} = V_{CEV}$ T_c = 100 °C			0.2 1	mA mA
I_{CEV}	Collector Cut-off Current (I_B = 0)	$V_{CE} = V_{CEV}$ V_{BE} = -1.5 V $V_{CE} = V_{CEV}$ V_{BE} = -1.5 V T_c =100°C			0.2 1	mA mA
I_{EBO}	Emitter Cut-off Current (I_C = 0)	V_{BE} = 5 V			1	mA
$V_{CEO(sus)}$*	Collector-Emitter Sustaining Voltage	I_C = 200 mA L = 25 mH	450			V
V_{EBO}	Emitter Base Voltage (I_C = 0)	I_E = 50 mA	7			V
$V_{CE(sat)}$*	Collector-Emitter Saturation Voltage	I_C = 5 A I_B = 0.5 A I_C = 5 A I_B = 0.5 A T_c =100°C I_C =10 A I_B = 2 A I_C =10 A I_B = 2 A T_c =100°C		0.8 0.5 	 2.8 2	V V V V
$V_{BE(sat)}$*	Base-Emitter Saturation Voltage	I_C = 5 A I_B = 0.5 A I_C = 5 A I_B = 0.5 A T_c =100°C I_C =10 A I_B = 2 A I_C =10 A I_B = 2 A T_c =100°C		0.9 1.1 	 1.5 1.5	V V V V
di_c/dt	Rate of rise on-state Collector Current	V_{CC} = 300 V R_C = 0 t_p= 3 µs I_{B1} = 0.75 A T_j =25°C I_{B1} = 0.75 A T_j =100°C I_{B1} = 3 A T_j =100°C	 45 100	 60 	 	 A/µs A/µs A/µs
V_{CE}(3µs)	Collector-Emitter Dynamic Voltage	V_{CC} = 300 V R_C = 60 Ω I_{B1} = 0.75 A T_j =25°C I_{B1} = 0.75 A T_j =100°C		 2.1 	 8	 V V
V_{CE}(5µs)	Collector-Emitter Dynamic Voltage	V_{CC} = 300 V R_C = 60 Ω I_{B1} = 0.75 A T_j =25°C I_{B1} = 0.75 A T_j =100°C		 1.1 	 4	 V V
t_s t_f t_c	Storage Time Fall Time Cross Over Time	I_C = 5 A V_{CC} = 50 V V_{BB} = - 5 V R_{BB} = 1.2 Ω V_{clamp} = 400 V I_{B1} = 0.5 A L = 0.5 mH		0.8 0.05 0.08		µs µs µs
t_s t_f t_c	Storage Time Fall Time Cross Over Time	I_C = 5 A V_{CC} = 50 V V_{BB} = - 5 V R_{BB} = 1.2 Ω V_{clamp} = 400 V I_{B1} = 0.5 A L = 0.5 mH T_j =100°C			1.8 0.1 0.18	µs µs µs
V_{CEW}	Maximum Collector Emitter Voltage without Snubber	IC = 5 A V_{CC} = 50 V V_{BB} = - 5 V R_{BB} = 1.2 Ω V_{clamp} = 400 V I_{B1} = 0.5 A L = 0.5 mH T_j =125°C	500			V
t_s t_f t_c	Storage Time Fall Time Cross Over Time	I_C = 5 A V_{CC} = 50 V V_{BB} = 0 R_{BB} = 0.3 Ω V_{clamp} = 400 V I_{B1} = 0.5 A L = 0.5 mH		1.5 0.04 0.07		µs µs µs

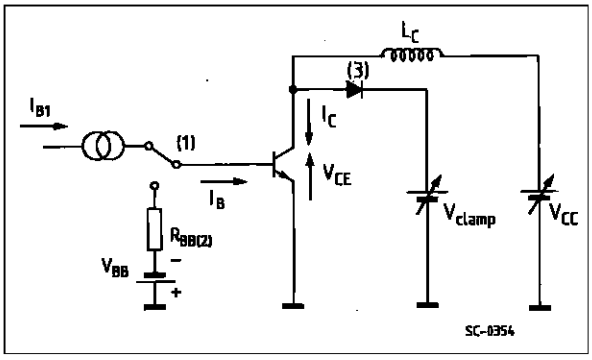
ELECTRICAL CHARACTERISTICS (continued)

Symbol	Parameter	Test Conditions		Min.	Typ.	Max.	Unit
t_s t_f t_c	Storage Time Fall Time Cross Over Time	I_C = 5 A V_{BB} = 0 V_{clamp} = 400 V L = 0.5 mH	V_{CC} = 50 V R_{BB} = 0.3 Ω I_{B1} = 0.5 A T_j =100°C			3 0.15 0.25	µs µs µs
V_{CEW}	Maximum Collector Emitter Voltage without Snubber	IC = 5 A V_{BB} = 0 V_{clamp} = 400 V L = 0.5 mH	V_{CC} = 50 V R_{BB} = 0.3 Ω I_{B1} = 0.5 A T_j =125°C	500			V
t_s t_f t_c	Storage Time Fall Time Cross Over Time	I_C = 10 A V_{BB} = -5 V V_{clamp} = 400 V L = 0.25 mH	V_{CC} = 50 V R_{BB} =1.2 Ω I_{B1} = 2 A		1.9 0.06 0.12		µs µs µs
t_s t_f t_c	Storage Time Fall Time Cross Over Time	I_C = 10 A V_{BB} = - 5 V V_{clamp} = 400 V L = 0.25 mH	V_{CC} = 50 V R_{BB} =1.2 Ω I_{B1} = 2 A T_j =100°C			3.2 0.12 0.3	µs µs µs
V_{CEW}	Maximum Collector Emitter Voltage without Snubber	ICWoff = 15 A V_{BB} = - 5 V L = 0.17 mH T_j =125°C	V_{CC} = 50 V R_{BB} = 1.2 Ω I_{B1} = 3 A	400			V

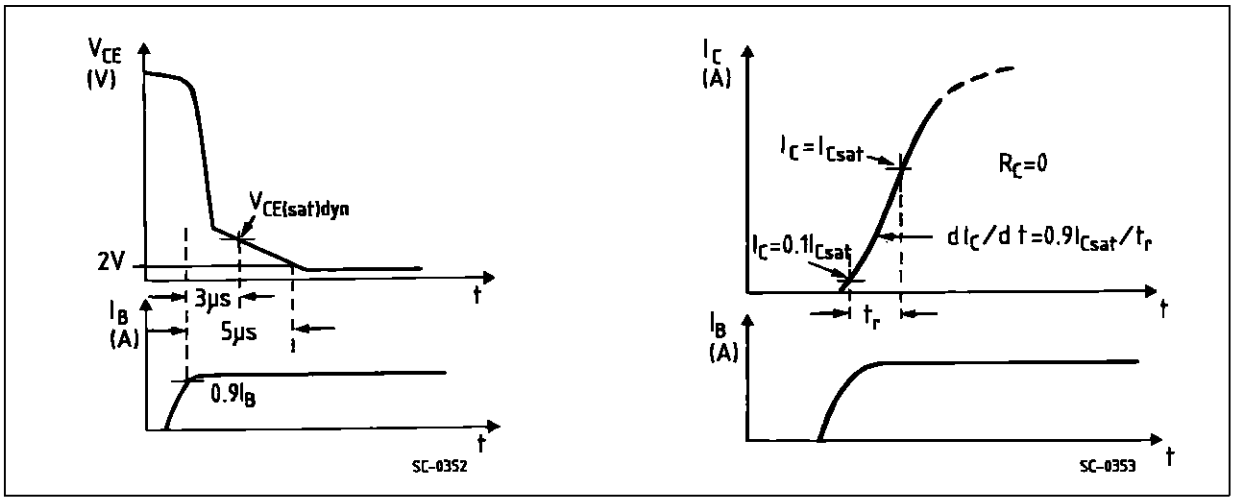
Turn-on Switching Test Circuit



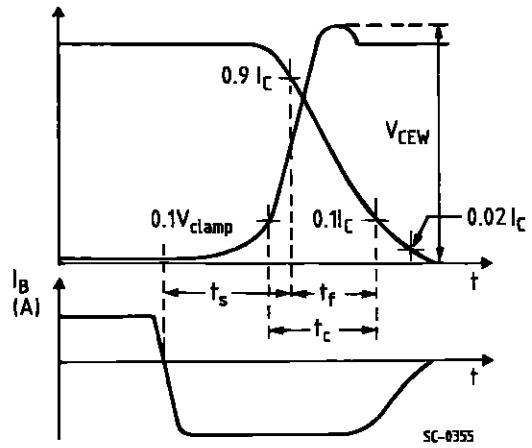
Turn-off Switching Test Circuit



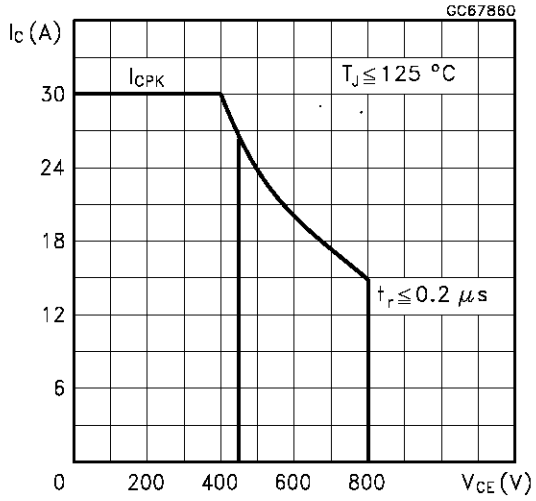
Turn-on SwitchingTest Waveforms.



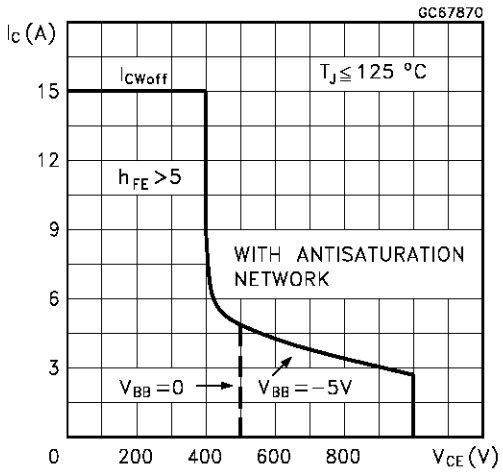
Turn-off SwitchingTest Waveforms (inductive load).



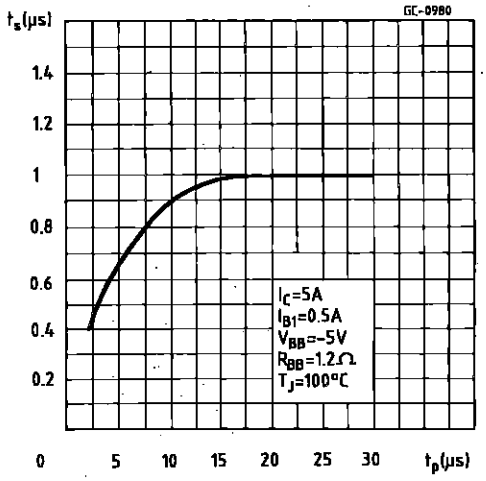
Forward Biased Safe Operating Areas.



Reverse Biased Safe Operating Area



Storage Time Versus Pulse Time.



TO-218 (SOT-93) MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	4.7		4.9	0.185		0.193
C	1.17		1.37	0.046		0.054
D		2.5			0.098	
E	0.5		0.78	0.019		0.030
F	1.1		1.3	0.043		0.051
G	10.8		11.1	0.425		0.437
H	14.7		15.2	0.578		0.598
L2	–		16.2	–		0.637
L3		18			0.708	
L5	3.95		4.15	0.155		0.163
L6		31			1.220	
R	–		12.2	–		0.480
Ø	4		4.1	0.157		0.161